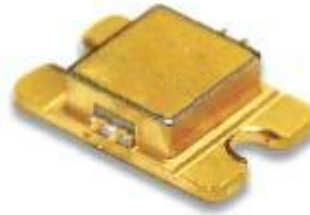


Performance

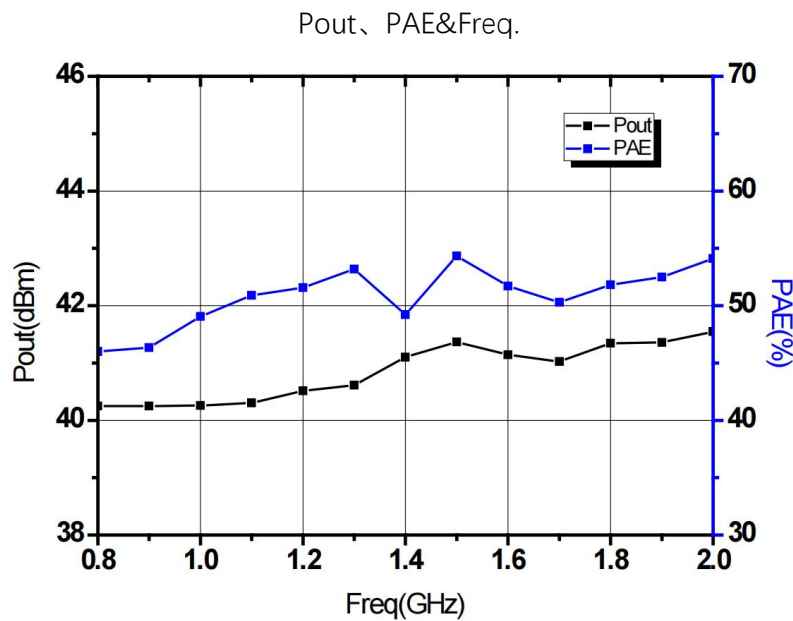
- Technology: 0.25um Power GaN HEMT
- Frequency: 0.8~2.0GHz
- Typical Pout : 40dBm
- Typical Gain: 26dB
- Typical PAE: 50%
- Bias: 28V/-2.4V
- Package: Metal Ceramic



Electrical Specifications (TA=25°C, Vd=28V, Vg=-2.4V, F: 0.8~2.0GHz, Pin=14dBm)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	40	41	-	dBm
Gp	Power Gain		26	-	dB
η_{add}	Power Added Efficiency	45	50	-	%
ΔGp	Gain Flatness	-1.0	-	+1.0	dB

Test Curves



Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	32V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	225°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~150°C	

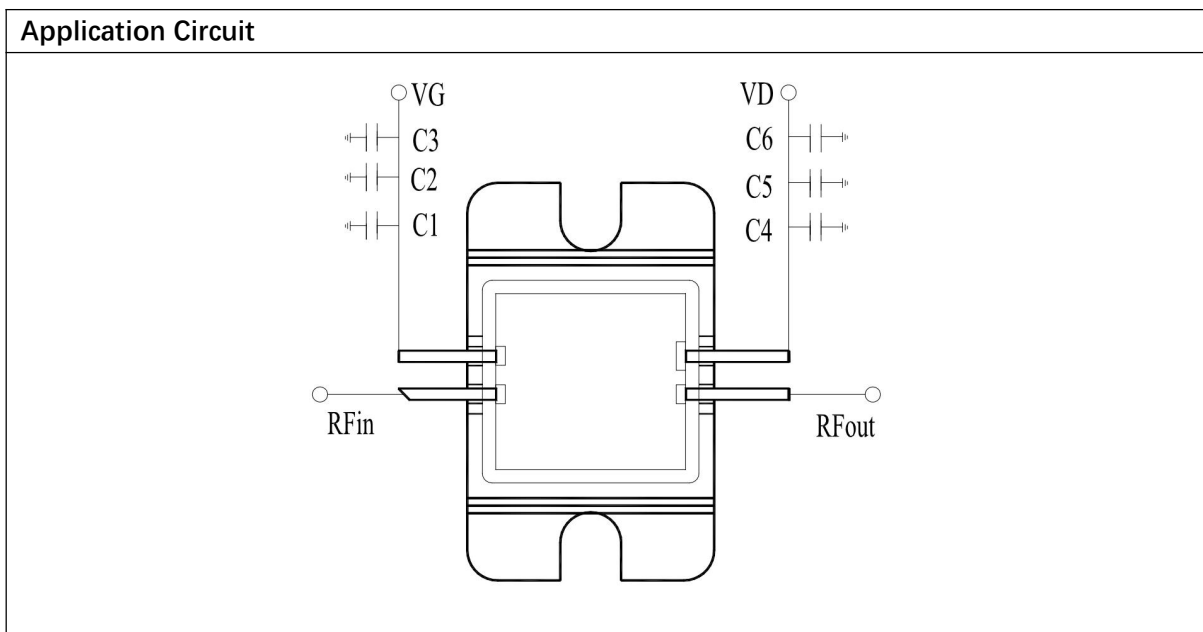
【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing

The image shows two technical drawings of a GaN Transistor. The top drawing is a top view, and the bottom drawing is a side view. The top view shows a central square region with a dashed center line. Dimensions L1, L2, and L3 are indicated for the top edge. Dimensions W1, W2, and W3 are indicated for the width. Dimensions H1, H2, and H3 are indicated for the height. The side view shows the profile of the transistor with dimensions H1, H2, and H3.

Dimension Symbol

Symbol	Value (unit: mm)	
	Min.	Max.
L1	13.0	13.2
L2	3.2	3.4
L3	2.0	-
W1	21.0	21.3
W2	17.0	17.3
W3	0.6	0.8
H1	4.6	5.5
H2	0.10	0.13
H3	2.6	2.9



Note:

- (1) This product is an internal matching power amplifier module, and the input and output impedance values are both 50 ohms;
- (2) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (3) This product is a high-power device. It is necessary to pay attention to heat dissipation during use. The higher the case temperature, the shorter the service life. It is advisable to use the temperature not higher than 85 degrees;
- (4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.